







AM26LS32AC, AM26LS32AI, AM26LS32AM AM26LS33AC, AM26LS33AM

SLLS115G - OCTOBER 1980 - REVISED AUGUST 2023

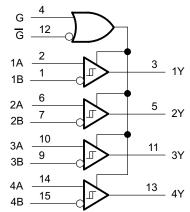
AM26LS32Ax, AM26LS33Ax Quadruple Differential Line Receivers

1 Features

- AM26LS32A Devices meet or exceed the requirements of ANSI TIA/EIA-422-B, TIA/ EIA-423-B, and ITU recommendations V.10 and
- AM26LS32A Devices have ±7-V Common-mode range with ±200-mV sensitivity
- AM26LS33A Devices have ±15-V common-mode range with ±500-mV sensitivity
- Input hysteresis 50 mV typical
- Operate from a single 5-V supply
- Low-power Schottky circuitry
- 3-State outputs
- Complementary output-enable inputs
- Input impedance 12 kΩ minimum
- Open input fail-safe

2 Applications

- High-reliability automotive applications
- **Factory automation**
- **ATM** and cash counters
- Smart grids
- AC and servo motor drives



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Pin numbers are for D, N, NS, or PW packages only.

Logic Diagram (Positive Logic)

3 Description

The AM26LS32Ax and AM26LS33Ax devices are quadruple differential line receivers for balanced and unbalanced digital data transmission. The enable function is common to all four receivers and offers a choice of active-high or active-low input. The 3-state outputs permit connection directly to a bus-organized system. When the inputs are open, the fail-safe design makes sure the outputs always are high.

Compared to the AM26LS32 and the AM26LS33, the AM26LS32A and AM26LS33A incorporate an additional stage of amplification to improve sensitivity. The input impedance has been increased, resulting in less loading of the bus line. The additional stage has increased propagation delay; however, this does not affect interchangeability in most applications.

The AM26LS32AC and AM26LS33AC are characterized for operation from 0°C to 70°C. The AM26LS32AI is characterized for operation from -40°C to 85°C. The AM26LS32AM and AM26LS33AM are characterized for operation over the full military temperature range of -55°C to 125°C.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
AM26LS3xAC	PDIP (16)	19.3 mm × 9.4 mm
AM26LS32AI	SOIC (16)	9.9 mm × 6 mm
AM26LS32AC	SO (16)	10.2 mm × 7.8 mm
AMZOLOGIZAC	TSSOP (16)	5. mm × 6.4 mm
AM26LS3xAM	CDIP (16)	19.56 mm × 6.92 mm
AIVIZOLSSXAIVI	LCCC (20)	8.9 mm × 8.9 mm

- For all available packages, see the orderable addendum at the end of the data sheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.



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5 Pin Configuration and Functions

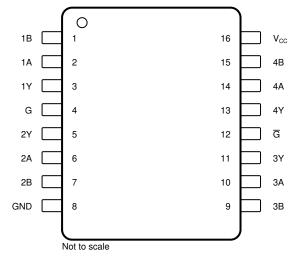
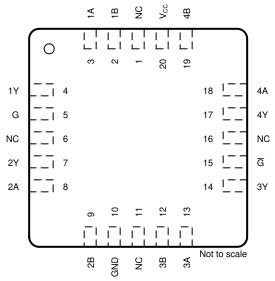


Figure 5-1. D, J, N, NS, and PW Package 16-Pin SOIC, CDIP, PDIP, SO, and TSSOP (Top View)



NC - No internal connection

Figure 5-2. FK Package, 20-Pin LCCC (Top View)

PIN		PIN		PIN			
NAME	SOIC, CDIP, PDIP, SO, TSSOP	LCCC	TYPE	DESCRIPTION			
1A	2	3	I	RS422/RS485 differential input (noninverting)			
1B	1	2	I	RS422/RS485 differential input (inverting)			
1Y	3	4	0	Logic level output			
2A	6	8	I	RS422/RS485 differential input (noninverting)			
2B	7	9	I	RS422/RS485 differential input (inverting)			
2Y	5	7	0	Logic level output			
3A	10	13	ı	RS422/RS485 differential input (noninverting)			
3B	9	12	I	RS422/RS485 differential input (inverting)			
3Y	11	14	0	Logic level output			
4A	14	18	I	RS422/RS485 differential input (noninverting)			
4B	15	19	ı	RS422/RS485 differential input (inverting)			
4Y	13	17	0	Logic level output			
G	12	15	I	Active-Low select			
G	4	5	I	Active-High select			
GND	8	10	_	Ground			
NC	_	1, 6, 11, 16	_	No internal connection			
V _{CC}	16	20	_	Power supply			



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT	
Supply voltage, V _{CC} ⁽²⁾	Any differential input Other inputs Perential input voltage, V _{ID} (3) Itinuous total power dissipation				
Input voltage V	ut voltage, V _I		±25	V	
Imput voitage, vi	Other inputs		7	V	
Differential input voltage, V _{ID} ⁽³⁾	·		±25	V	
Continuous total power dissipation	See Sec	tion 6.7			
Case temperature, T _C , FK package (60	s)		260	°C	
Lead temperature ⁽⁴⁾	D or N package (10 s)		260	°C	
Lead temperature(*)	J package (60 s)		300		
Storage temperature, T _{stg}	torage temperature, T _{stg}			°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) All voltage values, except differential voltages, are with respect to the network ground terminal.
- (3) Differential voltage values are at the noninverting (A) input terminals with respect to the inverting (B) input terminals.
- (4) 1.6 mm (1/16 inch) from case

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±500	\ \/
V _(ESD) Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±2000	v	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
\/	Supply voltage	AM26LS32AC, AM26LS32AI, AM26LS33AC	4.75	5	5.25	V
V _{CC}	Supply voltage	AM26LS32AM, AM26LS33AM	4.5	5	5.5	V
V _{IH}	High-level input voltage		2			V
V _{IL}	Low-level input voltage				0.8	V
\/	Common mode input voltage	AM26LS32A			±7	V
V _{IC}	Common-mode input voltage	AM26LS33A			±15	V
I _{OH}	High-level output current				-440	μA
I _{OL}	Low-level output current				8	mA
		AM26LS32AC, AM26LS33AC	0		70	
T _A	Operating free-air temperature	AM26LS32AI	-40		85	°C
		AM26LS32AM, AM26LS33AM	-55		125	



6.4 Thermal Information

			AM26LS3xAC, AM26LS32AI				AM26LS32AC			
THERMAL METRIC(1)		D (SOIC)	DR (SOIC- Reel)	N (PDIP)	NR (PDIP- Reel)	NS (SO)	NSR (SO- Reel)	PW (TSSOP)	PWR (TSSOP- Reel)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to- ambient thermal resistance	75.7	84.6	45.3	60.6	75.8	88.5	102.7	107.5	°C/W
$R_{\theta JC(top)}$	Junction-to- case (top) thermal resistance	35	43.5	32.7	48.1	32.9	46.2	37.8	38.4	°C/W
$R_{\theta JB}$	Junction-to- board thermal resistance	33.3	43.2	25.3	40.6	36.6	50.7	47.7	53.7	°C/W
ΤιΨ	Junction-to- top characterizat ion parameter	6.6	10.4	17.8	27.5	6	13.5	3	3.2	°C/W
ΨЈВ	Junction-to- board characterizat ion parameter	33	42.8	25.1	40.3	36.3	50.3	47.1	53.1	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over recommended ranges of V_{CC}, V_{IC}, and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TYP ⁽¹⁾	MAX	UNIT
V _{IT+}	Positive-going input threshold	V _O = V _{OH} min, I _{OH} = -440 μA	AM26LS32A			0.2	V
VIT+	voltage	VO - VOHITIIT, IOH440 μΑ	AM26LS33A			0.5	v
V _{IT} _	Negative-going input threshold	V _O = 0.45 V , I _{OI} = 8 mA	AM26LS32A	-0.2 ⁽²⁾			V
VIT-	voltage	VO = 0.43 V , IOL = 0 IIIA	AM26LS33A	-0.5 ⁽²⁾			V
V _{hys}	Hysteresis voltage (V _{IT+} – V _{IT–})				50		mV
V _{IK}	Enable-input clamp voltage	V _{CC} = MIN, I _I = -18 mA				-1.5	V
		V _{CC} = MIN, V _{ID} = 1 V,	AM26LS32AC, AM26LS33AC	2.7			
V _{OH}	High-level output voltage	$V_{I(G)} = 0.8 \text{ V}, I_{OH} = -440 \mu\text{A}$	AM26LS32AM, AM26LS32AI, AM26LS33AM	2.5			V
V _{OL}	Low-level output voltage	$V_{CC} = MIN, V_{ID} = -1 V,$	I _{OL} = 4 mA			0.4	V
VOL	Low-level output voltage	V _{I(G)} = 0.8 V	I _{OL} = 8 mA			0.45	
I _{OZ}	Off-state (high-impedance	V _{CC} = MAX	V _O = 2.4 V			20	μA
102	state) output current	A CC - INIVA	V _O = 0.4 V			-20	μΛ
l _l	Line input current	$V_I = 15 \text{ V}$, other input at -10 V to 1	15 V			1.2	mA
11	Line input current	$V_I = -15 \text{ V}$, other input at -15 V to	10 V			-1.7	ША
I _{I(EN)}	Enable input current	V _I = 5.5 V				100	μΑ
I _H	High-level enable current	V _I = 2.7 V				20	μΑ
IL	Low-level enable current	V _I = 0.4 V				-0.36	mA
r _i	Input resistance	V_{IC} = -15 V to 15 V, one input to a	12	15		kΩ	
Ios	Short-circuit output current ⁽³⁾	V _{CC} = MAX		-15		-85	mA
I _{CC}	Supply current	V _{CC} = MAX, all outputs disabled			52	70	mA

⁽¹⁾ All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, and $V_{IC} = 0$.

⁽²⁾ The algebraic convention, in which the less positive (more negative) limit is designated as minimum, is used in this data sheet for threshold levels only.

⁽³⁾ Not more than one output must be shorted to ground at a time, and duration of the short circuit must not exceed one second.



6.6 Switching Characteristics

 C_L = 15 pF, V_{CC} = 5 V, and T_A = 25°C (see Section 7; unless otherwise noted)

	PARAMETER	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		20	35	ns
t _{PHL}	Propagation delay time, high-to-low-level output		22	35	ns
t _{PZH}	Output enable time to high level		17	22	ns
t _{PZL}	Output enable time to low level		20	25	ns
t _{PHZ}	Output disable time from high level		21	30	ns
t _{PLZ}	Output disable time from low level		30	40	ns

⁽¹⁾ All typical values are at V_{CC} = 5 V, T_A = 25°C, and V_{IC} = 0.

6.7 Dissipation Ratings

PACKAGE	T _A ≤ 25°C POWER RATING	DERATION FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 125°C POWER RATING	
FK	1375 mW	11 mW/°C	880 mW	275 mW	
J	1375 mW	11 mW/°C	880 mW	275 mW	



6.8 Typical Characteristics

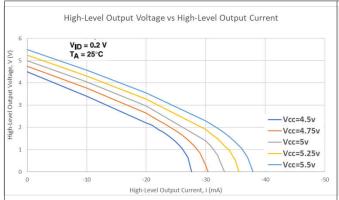


Figure 6-1. High-Level Output Voltage vs High-Level Output Current

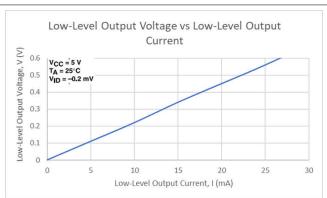


Figure 6-2. Low-Level Output Voltage vs Low-Level
Output Current

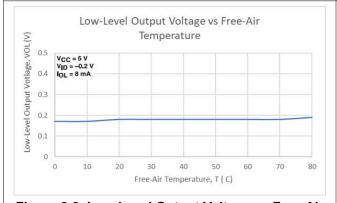


Figure 6-3. Low-Level Output Voltage vs Free-Air Temperature

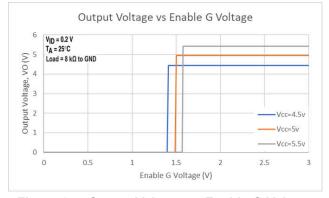


Figure 6-4. Output Voltage vs Enable G Voltage

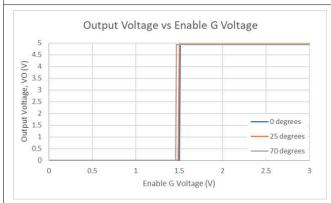


Figure 6-5. Output Voltage vs Enable G Voltage

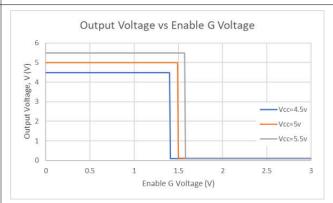


Figure 6-6. Output Voltage vs Enable G Voltage

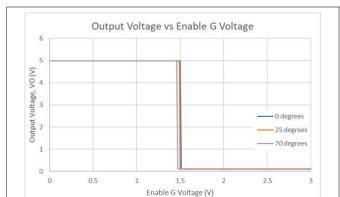


Figure 6-7. Output Voltage vs Enable G Voltage

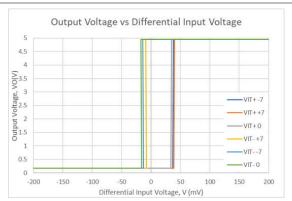


Figure 6-8. AM26LS32A Output Voltage vs Differential Input Voltage

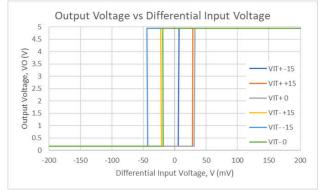
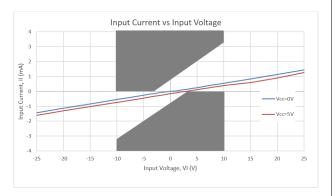


Figure 6-9. AM26LS33A Output Voltage vs Differential Input Voltage



The unshaded area shows requirements of paragraph 4.2.1 of ANSI Standards EIA/TIA-422-B and EIA/TIA-423-B.

Figure 6-10. Input Current vs Input Voltage



7 Parameter Measurement Information

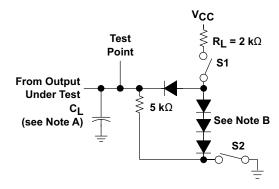


Figure 7-1. Test Circuit

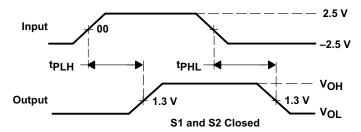


Figure 7-2. Voltage Waveforms For t_{PLH}, t_{PHL}

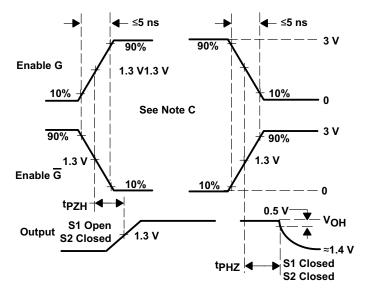
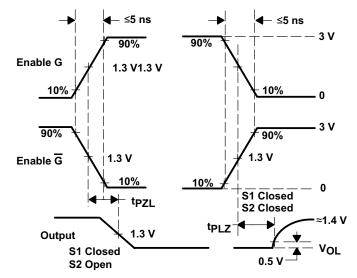
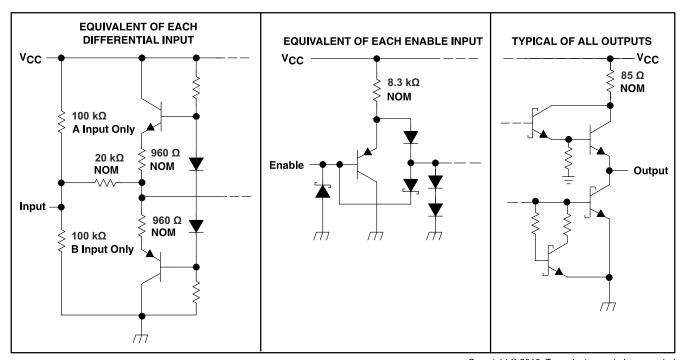


Figure 7-3. Voltage Waveforms For t_{PHZ}, t_{PZH}



- A. CL includes probe and jig capacitance.
- B. All diodes are 1N3064 or equivalent.
- C. Enable G is tested with \overline{G} high, \overline{G} is tested with G low.

Figure 7-4. Voltage Waveforms For t_{PLZ} , t_{PZL}



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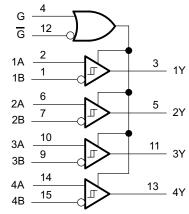
Figure 7-5. Schematics of Inputs and Outputs

8 Detailed Description

8.1 Overview

The AM26LS32 is a quadruple-differential line receiver that meets the necessary requirements for NSI TIA/EIA-422-B, TIA/EIA-423-B, and ITU Recommendation V.10 and V.11. This device allows a low-power or low-voltage MCU to interface with heavy machinery, subsystems, and other devices through long wires of up to 1000 m, giving any design a reliable and easy-to-use connection. As any RS422 interface, the AM26LS32 works in a differential voltage range, which enables very good signal integrity.

8.2 Functional Block Diagram



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Figure 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

The device can be configured using the G and \overline{G} logic inputs to select receiver output. The high voltage or logic 1 on the G pin allows the device to operate on an active-high, and having a low voltage or logic 0 on the G enables active low operation. These are simple ways to configure the logic to match that of the receiving or transmitting controller or microprocessor.

8.4 Device Functional Modes

The receivers implemented in these RS422 devices can be configured using the G and \overline{G} logic pins to be enabled or disabled. This allows users to ignore or filter out transmissions as desired.

ENABLES(1) OUTPUT⁽¹⁾ **DIFFERENTIAL** A-B Υ G $\overline{\mathbf{G}}$ Χ Н Н $V_{ID} \ge V_{IT+}$ Х L Н ? Н Χ $V_{\mathsf{IT-}} \leq V_{\mathsf{ID}} \leq V_{\mathsf{IT+}}$? Х L Н Χ L $V_{ID} \leq V_{IT-}$ Χ L L Х L Н Ζ Н Χ Н Open

L

Table 8-1. Function Table, Each Receiver

(1) H = High level, L = Low level, X = Irrelevant, Z = High impedance (off), ? = Indeterminate

Х

Н



9 Application and Implementation

Note

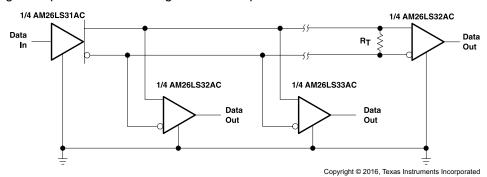
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

When using AM26LS32A as a receiver, the AM26LS31AC can allow multiple AM26LS32As to be used causing an increase in the amount of outputs.

9.2 Typical Application

Figure 9-1 shows a configuration with no termination. Although reflections are present at the receiver inputs at a data signaling rate of 200 kbps with no termination, the RS-422-compliant receiver reads only the input differential voltage and produces a clean signal at the output.



[†]R_T equals the characteristic impedance of the line.

Figure 9-1. Application Diagram

9.2.1 Design Requirements

Resistor and capacitor (if used) termination values are shown for each laboratory experiment, but vary from system to system. For example, the termination resistor, R_T , must be within 20% of the characteristic impedance, Z_O , of the cable and can vary from about 80 Ω to 120 Ω .

9.2.2 Detailed Design Procedure

Add a V_{CC} bypass capacitor (0.1 μ F or more). Either enable (G pin) input can turn on the receivers, so connect the desired enable to a compatible logic line output. The other enable input must be tied to the inactive state supply rail. If the receivers must always be active, then connect both enables to the supply rail such that at least one is set to an active-state rail. V_{CC} must be 5 V within 10% and logic inputs must provide TTL-compatible voltage levels A & B Inputs can lead to an external connector or can be left unconnected. The last receiver on a cable requires termination, either on-board or use as an external resistor. Unused Y outputs can be left unconnected.



9.2.3 Application Curve

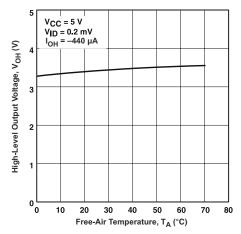


Figure 9-2. High-Level Output Voltage vs Free-Air Temperature

9.3 Power Supply Recommendations

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies.

9.4 Layout

9.4.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the
 operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance
 power sources local to the analog circuitry.
- Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.



9.4.2 Layout Example

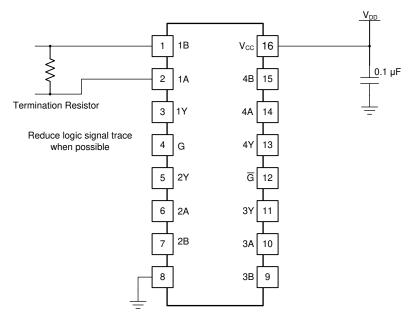


Figure 9-3. Layout with PCB Recommendations



10 Device and Documentation Support

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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10.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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